Shi

I hereby codify that this code spondence is being deposited with the U.S. Postal Service with sufficient postal Brist Class Mail, in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, or the date shown below.

Dated: June 3, 2004 Signature:

Paul B. Stephens

Docket No.: 30205/37980A

(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Seon Y. Cha

Application No.: 10/663,892

Art Unit: 2812

Filed: September 16, 2003

Examiner: J. Jey Tsai

For: Magnetic Random Access Memory Having

Transistor of Vertical Structure with Writing Line Formed on an Upper Portion of the Magnetic

Tunnel Junction Cell

AMENDMENT UNDER 37 CFR §1.312

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

INTRODUCTORY COMMENTS

Please amend the above-identified U.S. patent application as follows:

Amendments to the Specification begin on page 2 of this paper.

Remarks begin on page 3 of this paper.